

Publikačný seminár

J. Kuzmík:

Growth and Properties of N-Polar InN/InAlN Heterostructures

Phys. Stat. Solidi A

B. Zaťko:

Study of Schottky barrier detectors based on a high quality 4H-SiC epitaxial layer with different thickness

Appl. Surf. Sci.

M. Sojková:

Correlation between the crystalline phase of molybdenum oxide and horizontal alignment

in thin MoS₂ films

J. Phys. Chem. C

High carrier mobility epitaxially aligned PtSe₂ films grown by one-zone selenization

Appl. Surf. Sci.

Čas: 7. 10. 2020 o 10:00 hod. Miesto: veľká zasadačka EIÚ SAV, miestnosť 101